

Alkali metal-assisted growth in metal-organic chemical vapor deposition of two-dimensional layered chalcogenides

○Yu Kobayashi¹, Shoji Yoshida², Toshifumi Irisawa³, Naoya Okada³, Lim Hong-En¹, Kenji Watanabe⁴, Takashi Taniguchi⁴, Yutaka Maniwa¹, Osamu Takeuchi², Hidemi Shigekawa², Yasumitsu Miyata^{1,*}

¹ Department of Physics, Tokyo Metropolitan University, Hachioji, Tokyo 192-0397, Japan,

² Faculty of Pure and Applied Sciences, University of Tsukuba, Tsukuba, Ibaraki 305-8573, Japan,

³ Nanoelectronics Research Institute, National Institute of Advanced Industrial Science and Technology (AIST), Tsukuba, Ibaraki 305-8568, Japan,

⁴ National Institute for Materials Science, 1-1 Namiki, Tsukuba, Ibaraki 305-0044, Japan

Metal organic chemical vapor deposition (MOCVD) is one of the most powerful ways to prepare large-scale and uniform transition metal dichalcogenide (TMDC) atomic-layers and their heterostructures[1-3]. So far, the progress in vapor phase growth have been achieved by the use of metal organic precursors and additional growth promoters such as alkali metal halides. Although several works have been reported, the roles of the promoter remain unclear. It is therefore crucial to understand and control the effects of promoter to achieve better growth.

Here, by using alkali metal compounds as promoters, we report a high-quality TMDC growth with MOCVD. We found that the introduction of alkali metals improves various parameters, which includes grain size, uniformity of layer number, nucleation density, and defect density of TMDCs such as MoS₂, WS₂, MoSe₂, and WSe₂ monolayers. Besides, the alkali metal promoters work also on the exfoliated graphite and hexagonal boron nitride, the van der Waals surfaces, in addition to SiO₂ and sapphire. Our results suggest that the alkali metals may play a role in aiding the formation of intermediate products composed of alkali metals and transition metals rather than dehydration and/or substrate surface modification. The present findings pave way for the simple and rapid preparation of large scale, high quality TMDCs, and TMDC-based heterostructures.

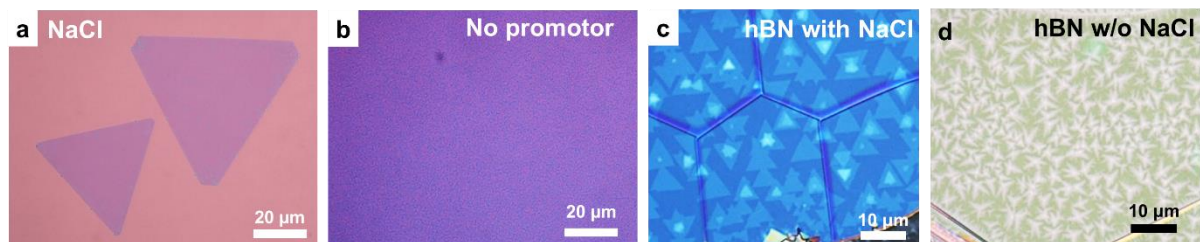


Figure 1. Optical images of MOCVD grown WS₂ (a) with and (b) without NaCl on SiO₂/Si, and (c) with and (d) without NaCl on hBN.

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Corresponding Author: Y. Miyata, Tel: +81-42-677-2508,

Web: <http://www.comp.tmu.ac.jp/miyata/index.html>, E-mail: y Miyata@tmu.ac.jp